

### **Description**

The DMN4031SSD uses advanced trench technology

to provide excellent R<sub>DS(ON)</sub>, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



SOP-8

#### **General Features**

 $V_{DS} = 40V I_{D} = 12A$ 

 $R_{DS(ON)}$  < 16m $\Omega$  @ V<sub>GS</sub>=10 V

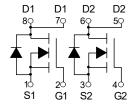
 $R_{DS(ON)}$  < 24m $\Omega$  @  $V_{GS}$ =4.5V

# **Application**

Battery protection

Load switch

Uninterruptible power supply



**Dual N-Channel MOSFET** 

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
DMN4031SSD	SOP-8	HXY MOSFET	3000

# Absolute Maximum Ratings@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	40	V
V <sub>GS</sub>	Gate-Source Voltage	<u>+</u> 20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	12	А
I <sub>D</sub> @T <sub>A</sub> =70°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	7	А
Ірм	Pulsed Drain Current <sup>1</sup>	40	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	2.9	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient <sup>3</sup>	65	°C/W



Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)				•		•
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1	1.5	2.0	V
Drain-Source On-State Resistance	В	V <sub>GS</sub> =10V, I <sub>D</sub> =8A	-	12.0	16	mΩ
Dialii-Source On-State Resistance	$R_{DS(ON)}$	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	18.9	24	mΩ
Forward Transconductance	<b>g</b> <sub>FS</sub>	V <sub>DS</sub> =5V,I <sub>D</sub> =8A	33	-	-	S
Dynamic Characteristics (Note4)			•			•
Input Capacitance	C <sub>lss</sub>	\/ -20\/\/ -0\/	-	964	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V, F=1.0MHz	-	109	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	r-1.0ivinz	-	96	-	PF
Switching Characteristics (Note 4)				•		
Turn-on Delay Time	t <sub>d(on)</sub>		-	5.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =20V, $R_L$ =2.5 $\Omega$	-	14	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{GEN}$ =3 $\Omega$	-	24	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS
Total Gate Charge	Qg	V 00V/1 0A	-	22.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=20V,I_{D}=8A,$	-	3.5	-	nC
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =10V	-	5.3	-	nC
Drain-Source Diode Characteristics	- '		l .	ı		ı
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =9A	-	0.8	1.2	V



## **Typical Electrical and Thermal Characteristics (Curves)**

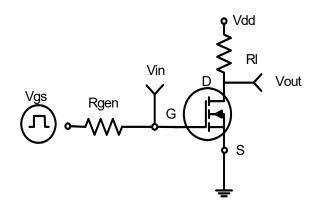


Figure 1:Switching Test Circuit

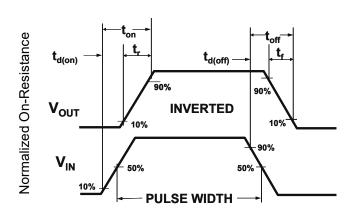
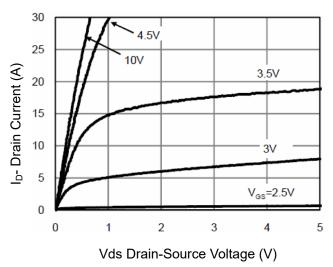
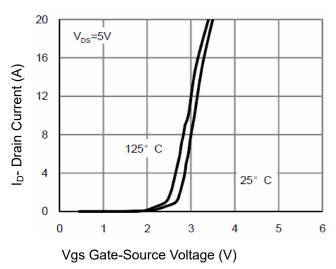


Figure 2:Switching Waveforms



**Figure 3 Output Characteristics** 



**Figure 4 Transfer Characteristics** 

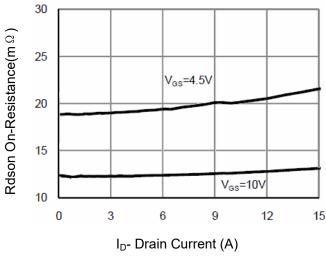


Figure 5 Drain-Source On-Resistance

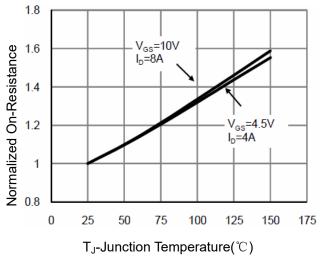


Figure 6 Drain-Source On-Resistance



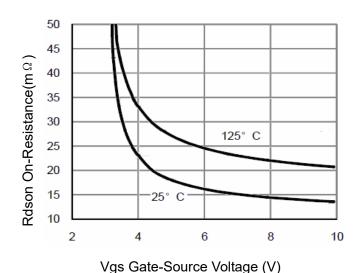


Figure 7 Rdson vs Vgs

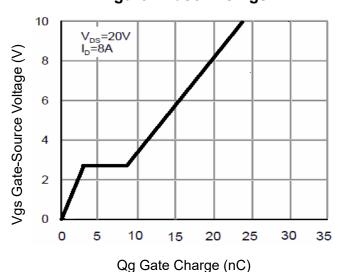


Figure 9 Gate Charge

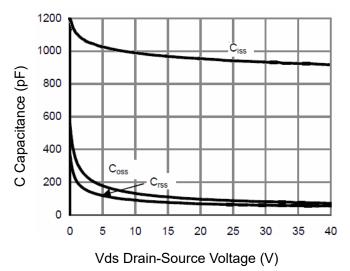


Figure 11 Capacitance vs Vds

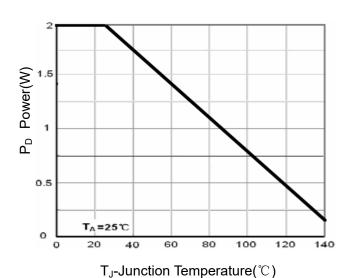


Figure 8 Power Dissipation

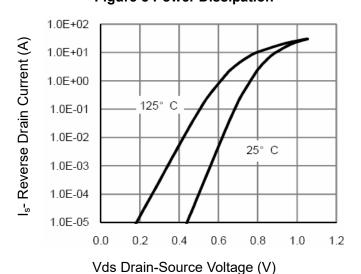
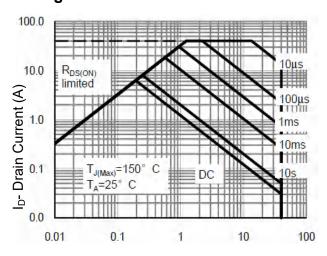


Figure 10 Source- Drain Diode Forward

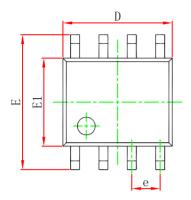


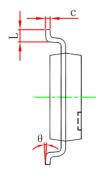
Vds Drain-Source Voltage (V)

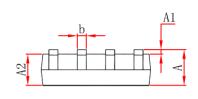
Figure 12 Safe Operation Area



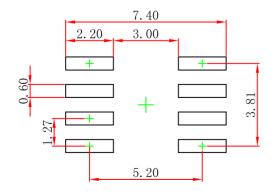
# **SOP-8 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0. 250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1. 270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0. 228	0.244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1. 270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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